

**APPENDIX A****"CLEAN" VERSION OF EACH PARAGRAPH/SECTION/CLAIM****37 C.F.R. § 1.121(b)(ii) AND (c)(i)**

Amend the Following Claims As Follows:

- C1 v 6. (Amended) The method defined in Claim 3 wherein said solid precursor material is a compound containing a metal selected from the group consisting of molybdenum, niobium, tantalum and tungsten.
- C2 10. (Amended) The method defined in Claim 3 wherein said solid precursor material is a compound containing a metal selected from the group consisting of molybdenum, niobium, tantalum and tungsten.
- / 11. (Amended) The method defined in claim 1 wherein:  
said solid precursor is a compound containing a metal selected from the group consisting of molybdenum, niobium, tantalum and tungsten;  
said liquid added to said solid precursor-containing bubbler apparatus has a vapor pressure less than  $10^{-8}$  Torr at room temperature;  
said solid precursor has a solubility in said liquid of less than 1000ppm;  
and said substrate to which said precursor is to be applied is selected from the group consisting of silicon, silicon dioxide or silicon nitride;  
said carrier gas being either a noble gas or ammonia
- v 12. (Amended) The method defined in Claim 1 wherein said metal in said compound forming said solid precursor is tungsten, said liquid is a silicon oil oligomer and said carrier gas is argon.

## APPENDIX B

## VERSION WITH MARKINGS TO SHOW CHANGES MADE

37 C.F.R. § 1.121(b)(iii) AND (c)(ii)

Amend the Following Claims As Follows:

6. (Amended) The method defined in Claim 3 wherein said solid precursor material is a compound containing a metal selected from the group consisting of molybdenum, niobium, tantalum and tungsten.
10. (Amended) The method defined in Claim 3 wherein said solid precursor material is a compound containing a metal selected from the group consisting of molybdenum, niobium, tantalum and tungsten.
11. (Amended) The method defined in claim 1 wherein:  
said solid precursor is a compound containing a metal selected from the group consisting of molybdenum, niobium, tantalum and tungsten;  
said liquid added to said solid precursor-containing bubbler apparatus has a vapor pressure less than  $10^{-8}$  Torr at room temperature;  
said solid precursor has a solubility in said liquid of less than 1000ppm;  
and said substrate to which said precursor is to be applied is selected from the group consisting of silicon, silicon dioxide or silicon nitride;  
said carrier gas being either a noble gas or ammonia
12. (Amended) The method defined in Claim 11 wherein said metal in said compound forming said solid precursor is tungsten, said liquid is a silicon oil oligomer and said carrier gas is argon.

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